

**IN THE CLAIMS**

Cancel claims 1 to 11 and consider new claims 12 to 31.

12. (New) A method for forming an integrated circuit comprising:
- forming a first interconnect layer over a substrate;
  - forming a second interconnect layer over the substrate;
  - depositing a passivation layer over the second interconnect layer;
  - forming an opening in the passivation layer that exposes a first electrical conductor of the second interconnect layer;
  - forming a wire bond pad that electrically connects to the first electrical conductor through the opening in the passivation layer; wherein the bond pad extends over the passivation layer and is positioned over a second electrical conductor associated with an underlying interconnect layer selected from a group consisting of the first interconnect layer and the second interconnect layer, wherein the second electrical conductor is not directly attached to the wire bond pad; and
  - attaching a wire bond to the wire bond pad.
13. (New) The method of claim 12 wherein the first interconnect layer includes copper.
14. (New) The method of claim 12, wherein the second interconnect layer includes copper.
15. (New) The method of claim 12, wherein the passivation layer is further characterized as a final passivation layer.
16. (New) The method of claim 12, wherein the wire bond pad includes aluminum.
17. (New) The method of claim 16, further comprising forming a barrier layer over the first electrical connector before forming the wire bond pad, wherein the barrier layer is positioned between the first electrical connector and the wire bond pad.

18. (New) The method of claim 12, wherein the second electrical conductor is for routing power supply voltage to electrical circuits on the integrated circuit.
19. (New) The method of claim 12, wherein a third conductor is formed using portions of the second interconnect layer and wherein the third conductor is not directly attached to the wire bond pad and routes a power supply voltage under the wire bond pad.
20. (New) A method for forming an integrated circuit comprising attaching a wire bond to a bond pad, wherein the bond pad electrically connects to a first conductor through an opening in a passivation layer, and wherein a portion of the bond pad extends over the passivation layer.
21. (New) The method of claim 20 wherein the first conductor is further characterized as a portion of an uppermost interconnect layer.
22. (New) The method of claim 21, wherein the wire bond is attached to the portion of the bond pad that extends the passivation layer.
23. (New) The method of claim 22, further comprising a second electrical conductor underlying the portion of the bond pad that extends over the passivation layer, wherein the second conductor is not directly attached to the bond pad.
24. (New) The method of claim 23, wherein the second electrical conductor is further characterized as a portion of an uppermost interconnect layer.
25. (New) The method of claim 23, wherein the second electrical conductor is further characterized a conductive region below the uppermost interconnect layer.
26. (New) The method of claim 23, wherein the second electrical conductor is further characterized as an interconnect layer.

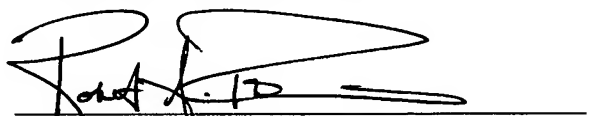
27. (New) A method of forming a semiconductor device comprising forming a wire bond pad that electrically connects to a first interconnect layer through an opening in a passivation layer; wherein the bond pad extends over the passivation layer and is positioned over a second electrical conductor associated with an underlying interconnect layer selected from a group consisting of the first interconnect layer and a second interconnect below the first interconnect layer, wherein the second electrical conductor is not directly attached to the wire bond pad.
28. (New) The method of claim 27, wherein the first interconnect layer includes copper.
29. (New) The method of claim 27, wherein the second interconnect layer includes copper.
30. (New) The method of claim 27, wherein the passivation layer is further characterized as a final passivation layer.
31. (New) The method of claim 27, wherein the wire bond pad includes aluminum.

SEND CORRESPONDENCE TO:

Motorola, Inc.  
Customer Number: 23125

Respectfully submitted,

By:



Robert A. Rodriguez  
Agent of Record  
Reg. No.: 45,049  
Telephone: (512) 996-6939  
Fax No.: (512) 996-6854